

**isc Silicon PNP Power Transistor**

**2N6421**

**DESCRIPTION**

- Continuous Collector Current- $I_C = -2A$
- Power Dissipation- $P_C = 35W @ T_C = 25^\circ C$
- Collector-Emitter Saturation Voltage-  
:  $V_{CE(sat)} = -0.75 V(Max) @ I_C = -1A$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

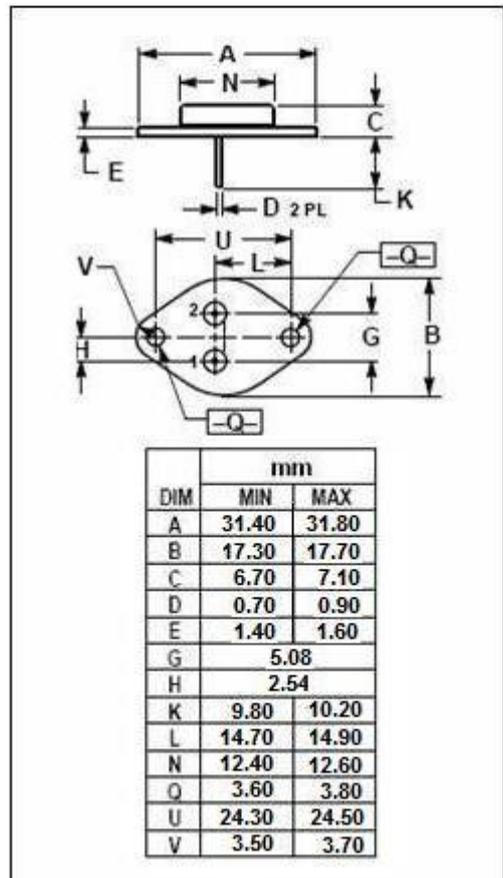
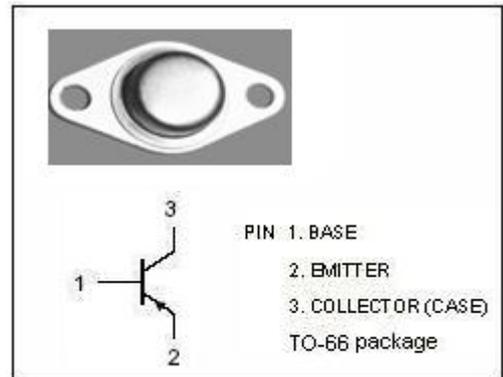
- Designed for high-speed switching and linear amplifier application for high-voltage operational amplifiers, switching regulators, converters, deflection stages and high fidelity amplifiers

**ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )**

| SYMBOL    | PARAMETER                                       | VALUE   | UNIT       |
|-----------|---|---------|------------|
| $V_{CBO}$ | Collector-Base Voltage                          | -375    | V          |
| $V_{CEO}$ | Collector-Emitter Voltage                       | -250    | V          |
| $V_{EBO}$ | Emitter-Base Voltage                            | -6      | V          |
| $I_C$     | Collector Current-Continuous                    | -2.0    | A          |
| $I_{CM}$  | Collector Current-Peak                          | -5.0    | A          |
| $I_B$     | Base Current                                    | -1.0    | A          |
| $P_C$     | Collector Power Dissipation@ $T_C = 25^\circ C$ | 35      | W          |
| $T_J$     | Junction Temperature                            | 150     | $^\circ C$ |
| $T_{stg}$ | Storage Temperature                             | -65~150 | $^\circ C$ |

**THERMAL CHARACTERISTICS**

| SYMBOL        | PARAMETER                            | MAX | UNIT         |
|---------------|--------------------------------------|-----|--------------|
| $R_{th\ j-c}$ | Thermal Resistance, Junction to Case | 5.0 | $^\circ C/W$ |



**isc Silicon PNP Power Transistor****2N6421****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

| SYMBOL         | PARAMETER                            | CONDITIONS                                    | MIN  | MAX   | UNIT |
|----------------|--------------------------------------|---|------|-------|------|
| $V_{CEQ(SUS)}$ | Collector-Emitter Sustaining Voltage | $I_C = -50\text{mA}$ ; $I_B = 0$              | -250 |       | V    |
| $V_{CE(sat)}$  | Collector-Emitter Saturation Voltage | $I_C = -1\text{A}$ ; $I_B = -0.125\text{A}$   |      | -0.75 | V    |
| $V_{BE(sat)}$  | Base-Emitter Saturation Voltage      | $I_C = -1\text{A}$ ; $I_B = -0.1\text{A}$     |      | -1.4  | V    |
| $V_{BE(on)}$   | Base-Emitter On Voltage              | $I_C = -1\text{A}$ ; $V_{CE} = -10\text{V}$   |      | -1.4  | V    |
| $I_{CEO}$      | Collector Cutoff Current             | $V_{CE} = -150\text{V}$ ; $I_B = 0$           |      | -5.0  | mA   |
| $I_{EBO}$      | Emitter Cutoff Current               | $V_{EB} = -6\text{V}$ ; $I_C = 0$             |      | -0.5  | mA   |
| $h_{FE-1}$     | DC Current Gain                      | $I_C = -0.1\text{A}$ ; $V_{CE} = -10\text{V}$ | 40   |       |      |
| $h_{FE-2}$     | DC Current Gain                      | $I_C = -1\text{A}$ ; $V_{CE} = -2\text{V}$    | 8    | 80    |      |
| $h_{FE-3}$     | DC Current Gain                      | $I_C = -1\text{A}$ ; $V_{CE} = -10\text{V}$   | 25   | 100   |      |